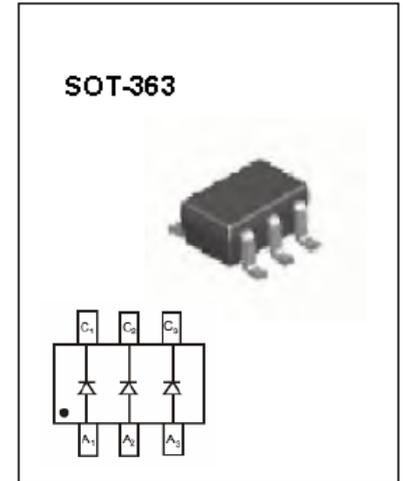
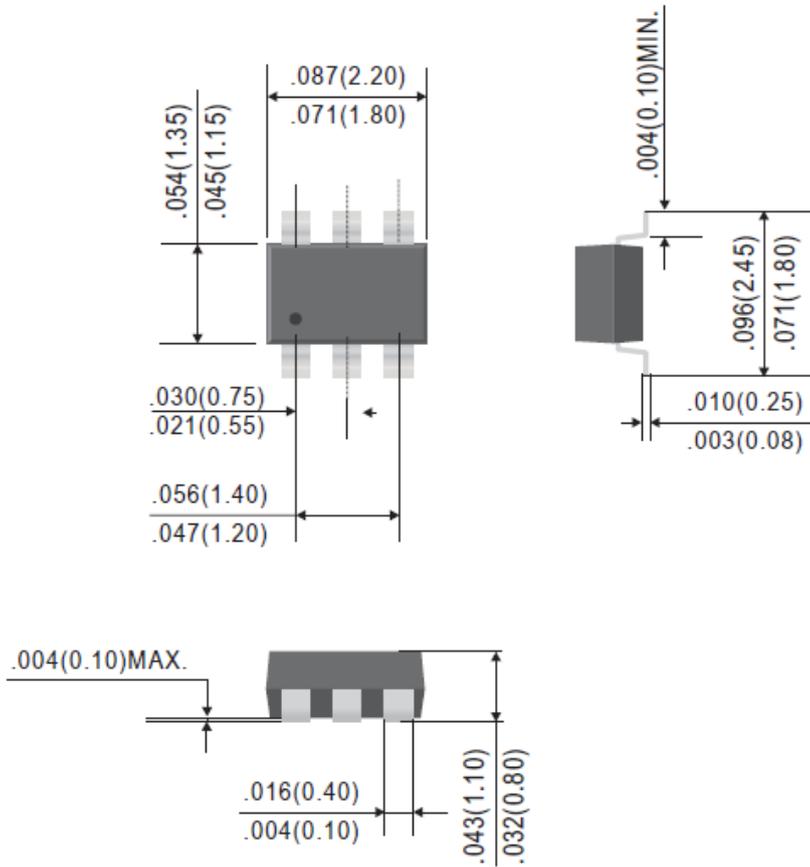




MMBD4148TW



Plastic-Encapsulate Diodes



Dimensions in inches and (millimeters)

FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance Power Dissipation
- Pb-Free package is available
- RoHS product for packing code suffix "G"
- Halogen free product for packing code suffix "H"
- Moisture Sensitivity Level 1

MARKING: KA2



Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V	
Peak Repetitive Reverse Voltage	V_{RRM}	75	V	
Working Peak Reverse Voltage	V_{RWM}			
DC Blocking Voltage	V_R			
RMS Reverse Voltage	$V_{R(RMS)}$	53	V	
Forward Continuous Current	I_{FM}	300	mA	
Average Rectified Output Current	I_O	150	mA	
Non-Repetitive Peak Forward Surge Current		@ $t = 1\mu\text{s}$	2	A
		@ $t = 1\text{s}$	1	
Power Dissipation	P_D	200	mW	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$	
Junction Temperature	T_J	150	$^\circ\text{C}$	
Storage Temperature Range	T_{STG}	-65~+150	$^\circ\text{C}$	

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)					
Parameter	Symbol	Test conditions	Min.	Max.	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=10\mu\text{A}$	75	—	V
Forward Voltage	V_F	$I_F=1\text{mA}$	—	0.715	V
		$I_F=10\text{mA}$	—	0.855	
		$I_F=50\text{mA}$	—	1	
		$I_F=150\text{mA}$	—	1.25	
Reverse Current	I_R	$V_R=75\text{V}$	—	1	μA
		$V_R=20\text{V}$	—	25	nA
Total capacitance	C_T	$V_R=0\text{V}$, $f=1\text{MHz}$	—	2	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=10\text{mA}$, $I_{rr}=0.1\times I_R$, $R_L=100\Omega$	—	4	ns

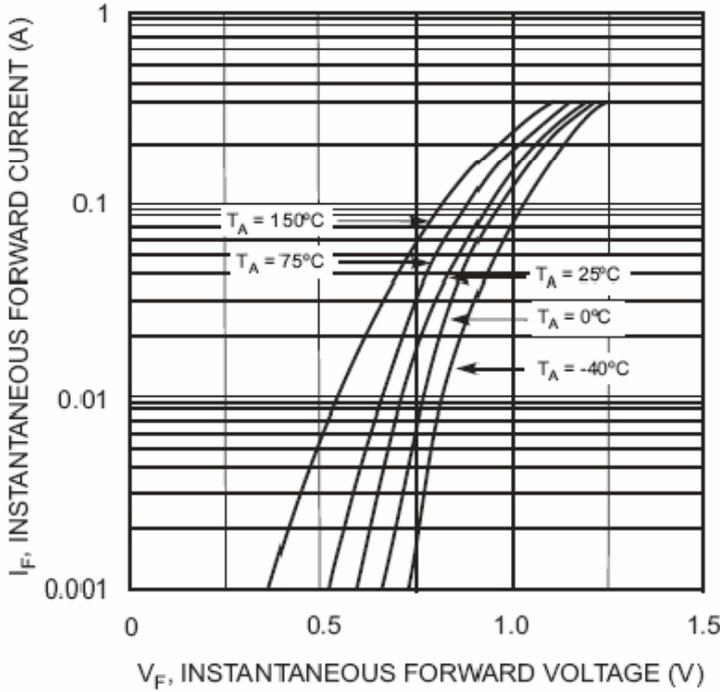


Fig. 2 Forward Characteristics

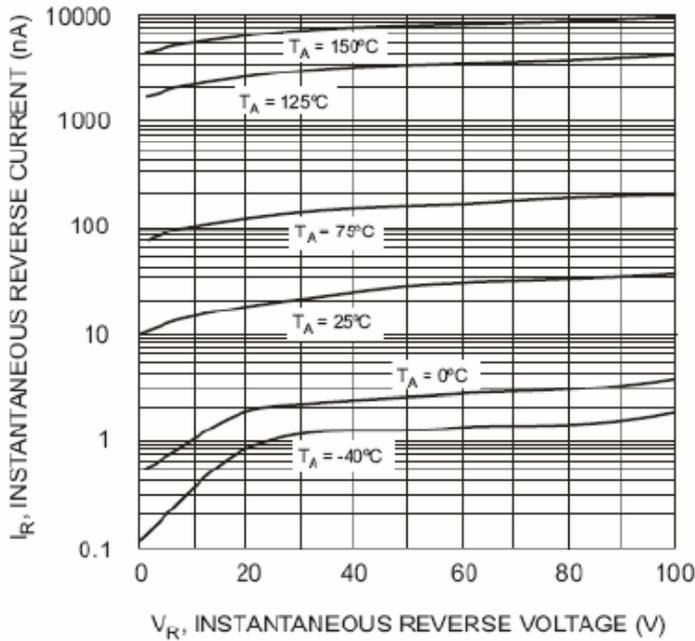


Fig. 3 Typical Reverse Characteristics

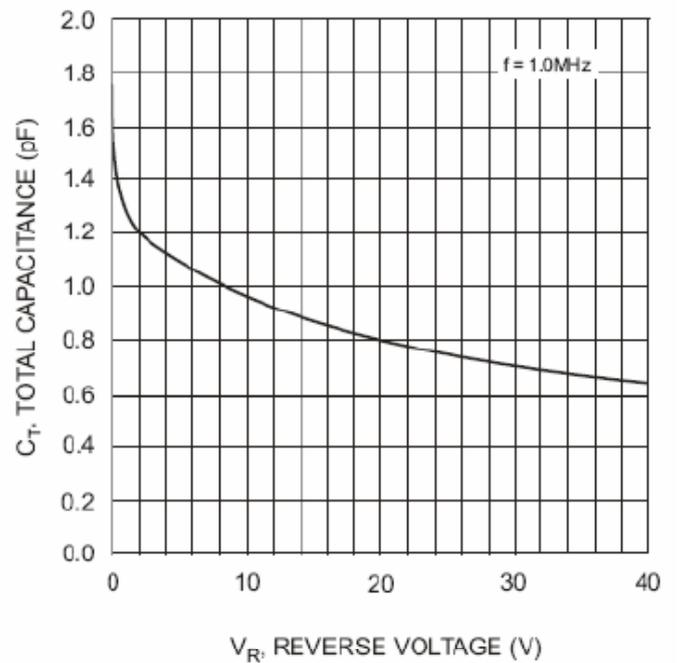


Fig. 4 Typical Capacitance vs. Reverse Voltage